

GaAs INTEGRATED CIRCUIT μ PG100P, μ PG101P

WIDE BAND AMPLIFIER CHIPS

DESCRIPTION

 μ PG100P and μ PG101P are GaAs integrated circuits designed as wide band amplifiers. Both devices are available in chip form.

 μ PG100P is low noise amplifier from 50 MHz to 3 GHz and μ PG101P is a medium power amplifier in the same frequency band. These devices are most suitable for the IF stage of microwave communication system and the measurement equipment.

FEATURES

• Wide band: f = 50 MHz to 3 GHz

ORDERING INFORMATION

PART NUMBER	FORM		
μPG100P	chip		
μPG101P	chip		

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

		μ PG100P	μ PG101P	
Drain Voltage	V_{DD}	+8	+10	V
Gate Voltage	Vgg	-8	-8	V
Input Voltage	V_{in}	−3 to +0.6	-5 to +0.6	V
Input Power	Pin	+15	+15	dBm
Total Power Dissipation	Ptot*1	1.5	1.5	W
Operating Temperature	Topr*2	-65 to +125	-65 to +125	°C
Storage Temperature	T _{stg}	-65 to +175	-65 to +175	°C

^{*1} Mounted with AuSn hard solder

^{*2} The temperature of base material baside the chip



ELECTRICAL CHARACTERISTICS (TA = 25 °C)³

 μ PG100P (V_{DD} = +5 V, V_{GG} = -5 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Current	loo	30	45	60	mA	RF OFF
Gate Current	Igg		0.7	1.5	mA	
Power Gain	Gp	14	16		dB	f = 0.05 to 3 GHz
Gain Flatness	⊿Gp			±1.5	dB	
Noise Figure	NF		2.7	3.5	dB	
Input Return Loss	RLin	7	10		dB	
Output Return Loss	RLout	7	10		dB	
Isolation	IsoL	30	40		dB	
Output Power at 1 dB Gain Compression Point	Po(1 dB)	+3	+6		dBm	

 μ PG101P (VDD = +8 V, VGG = -5 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Current	loo	70	100	140	mA	RF OFF
Gate Current	Igg		1.0	3.0	mA	
Power Gain	Gp	12	14		dB	f = 0.05 to 3 GHz
Gain Flatness	∆Gp			±1.5	dB	
Noise Figure	NF		5	7	dB	
Input Return Loss	RLin	6	8		dB	
Output Return Loss	RLout	6	8		dB	
Isolation	IsoL	30	40		dB	
Output Power at 1 dB Gain Compression Point	Po(1 dB)	+16	+18		dBm	

^{*3} These characteristics are based on performance of devices mounted in the standard package shown in Fig. 1.

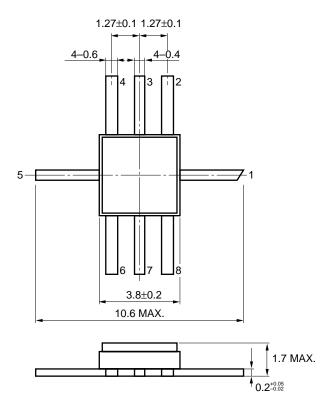
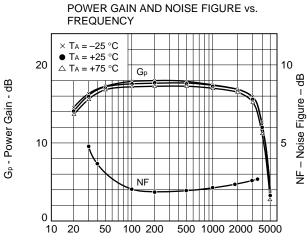
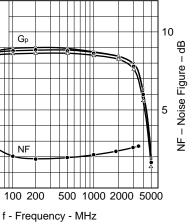


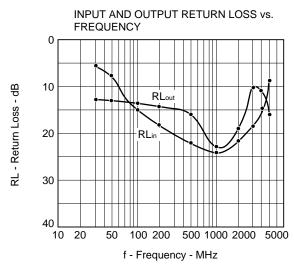
Fig. 1 8 Pin Ceramic Package

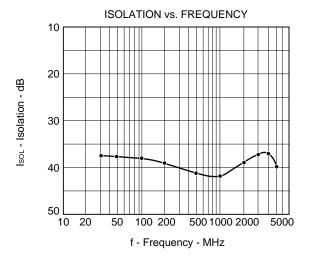
TYPICAL CHARACTERISTICS⁴

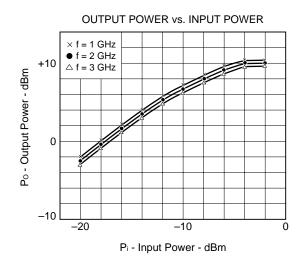
 μ PG100P (V_{DD} = +5 V, V_{GG} = -5 V)



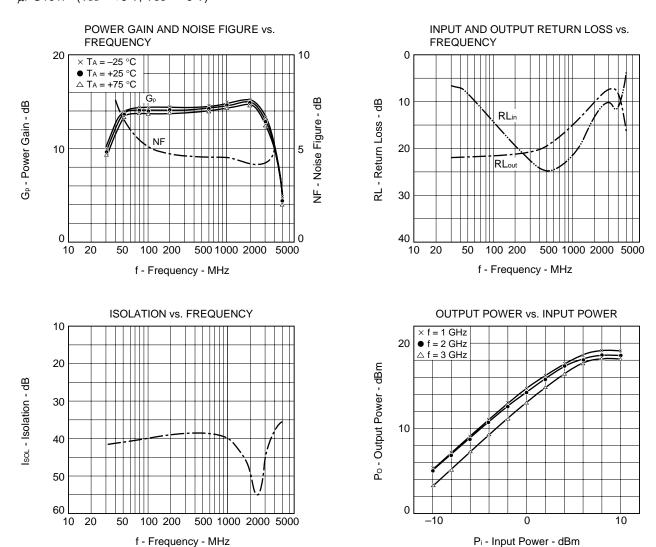








 μ PG101P (V_{DD} = +8 V, V_{GG} = -5 V)

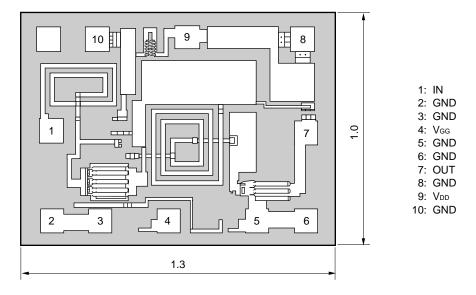


^{*4} These characteristics are measured for device mounted in the standard package shown in Fig. 1.



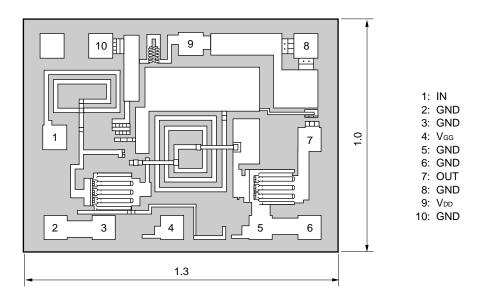
CHIP DIMENSIONS (Unit: mm)

 μ PG100P



Bonding Pad Size: $100 \mu m \times 100 \mu m$

 μ PG101P



Bonding Pad Size: $100 \, \mu \mathrm{m} \approx 100 \, \mu \, \mathrm{m}$



RECOMMENDED CHIP ASSEMBLY CONDITIONS

Die Attachment

 $\begin{array}{lll} \mbox{Atmosphere} & : \mbox{ N2 gas} \\ \mbox{Temperature} & : \mbox{ 320 \pm 5 °C} \end{array}$

AuSn Preform : $0.5 \times 0.5 \times 0.05^{t}$ (mm), 2 pcs.

* The hard solder such as AuSi or AuGe which has higher melting point than

AuSn should not be used.

Base Material : CuW, Cu, KV

* Other material should not be used.

Epoxy Die Attach is not recommended.

Bonding

Machine : TCB

* USB is not recommended

Wire : 30 μ m diameter Au wire

Temperature : 260 ± 5 °C Strength : 31 ± 3 g Atmosphere : N_2 gas

QUALITY ASSURANCE (Refer to GET-30116)

1. 100 % Tests

1-1 100 % DC and RF Probe

1-2 Visual Inspection

MIL-STD-883/Method 2010 Condition B

2. Tests on Sampling Basis

2-1 Bond Pull Tests (In case of recommended chip handling)

MIL-STD-883 Method 2011

5 samples/wafer and 20 points tested

Accept 0/Reject 1

2-2 Tests in Standard Package

Test the electrical characteristics of chips assembled into the standard package used for μ PG100B and μ PG101B.

5 samples/wafer tested

DC and RF measurement Accept 1/Reject 2

3. WARRANTEE

NEC has a responsibility of quality assurance for the products within 180 days after delivered to customers where these are handled properly and stored in the desicater with the flow of dry N_2 gas.

4. CAUTION

- 4-1 Take great care to prevent static electricity.
- 4-2 Be sure that Die Attach is performed in N2 atmosphere.

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Anti-radioactive design is not implemented in this product.

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